60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
60V	50mΩ @ V_{GS} = 10V	24A
	65mΩ @ V_{GS} = 4.5V	21A

Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$—Minimizes Power Losses
- Low Q_G—Minimizes Switching Losses
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMNH6042SPDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

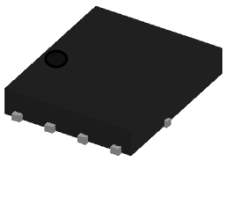
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

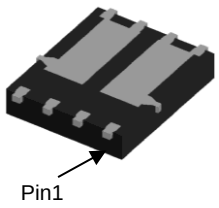
Mechanical Data

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

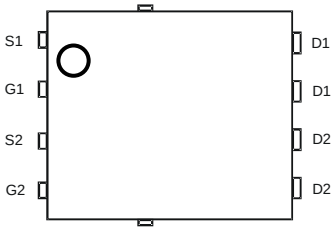
PowerDI5060-8 (Type C)



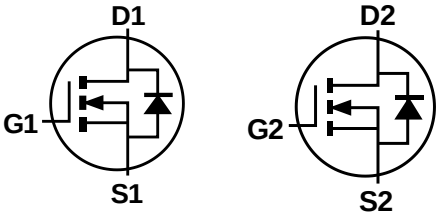
Top View



Bottom View



Pinout
Top View



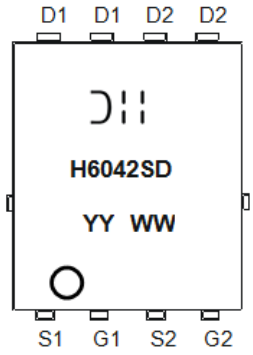
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMNH6042SPDQ-13	PowerDI5060-8 (Type C)	2500	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
H6042SD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 24 = 2024)
WW = Week (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	5.7 4.6	A
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T_C = +25°C T_C = +100°C	I_D	24 17	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	32	A
Maximum Continuous Body Diode Forward Current (Note 8)			I_S	24	A
Avalanche Current (Note 8) L = 10mH			I_{AS}	3.5	A
Avalanche Energy (Note 8) L = 10mH			E_{AS}	65	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\Theta JA}$	105	°C/W
	t<10s		54	
Total Power Dissipation (Note 6)		P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\Theta JA}$	51	°C/W
	t<10s		26	
Thermal Resistance, Junction to Case (Note 7)		$R_{\Theta JC}$	3.5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	34	50	mΩ	V_{GS} = 10V, I_D = 5.1A
		—	45	65		V_{GS} = 4.5V, I_D = 4.4A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 2.6A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{ISS}	—	584	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{OSS}	—	83	—	pF	
Reverse Transfer Capacitance	C_{RSS}	—	24	—	pF	
Gate Resistance	R_G	—	3.8	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_G	—	4.2	—	nC	V_{DS} = 44V, I_D = 5.2A
Total Gate Charge (V_{GS} = 10V)	Q_G	—	8.8	—	nC	
Gate-Source Charge	Q_{GS}	—	1.8	—	nC	
Gate-Drain Charge	Q_{GD}	—	1.8	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.4	—	ns	V_{GS} = 10V, V_{DS} = 30V, R_G = 6Ω, I_D = 1A
Turn-On Rise Time	t_R	—	1.9	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	10.1	—	ns	
Turn-Off Fall Time	t_F	—	4.5	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	12.9	—	ns	I_F = 2.6A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	5.4	—	nC	I_F = 2.6A, di/dt = 100A/µs

Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

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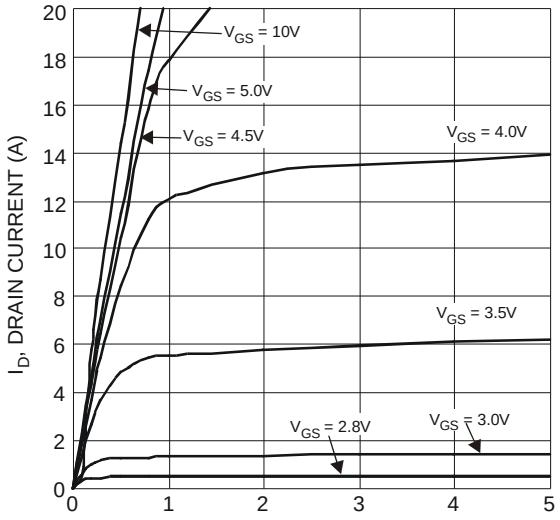


Figure 1 Typical Output Characteristics

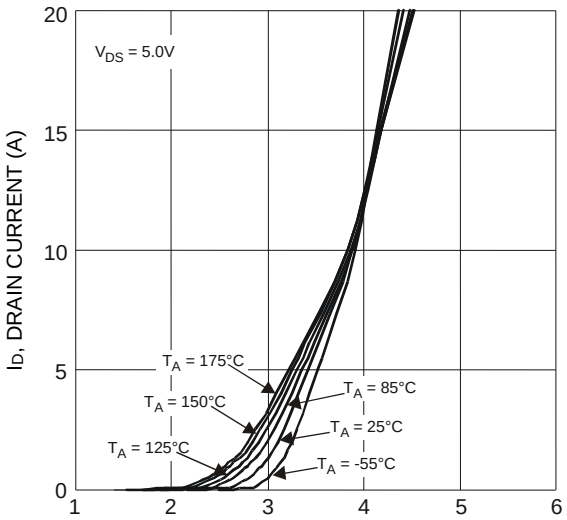


Figure 2 Typical Transfer Characteristics

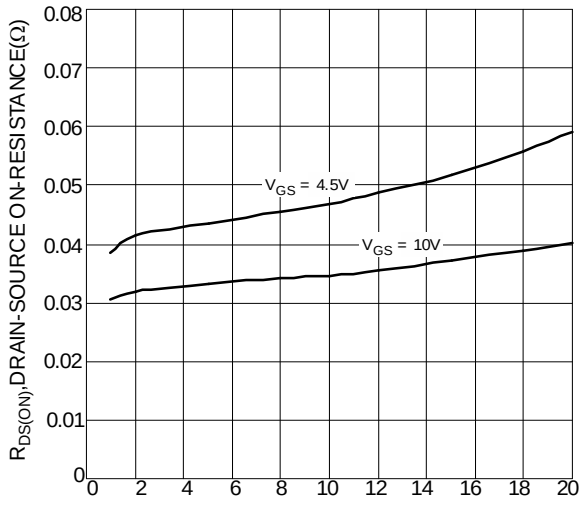


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

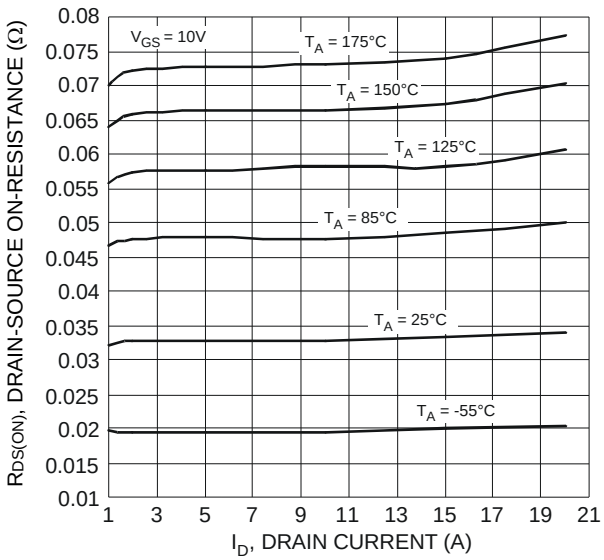


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

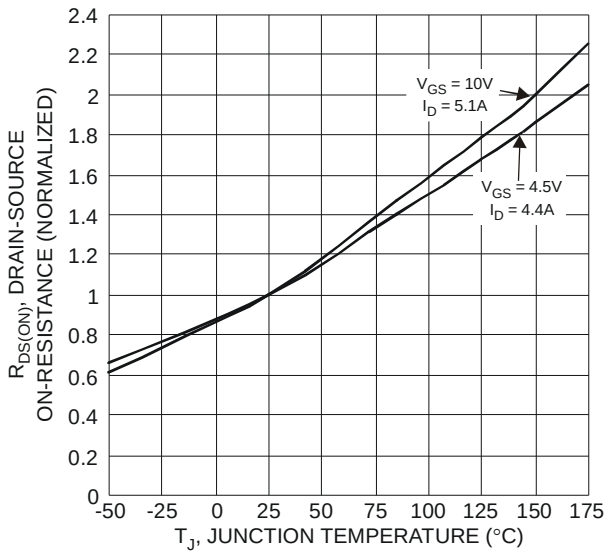


Figure 5 On-Resistance Variation with Temperature

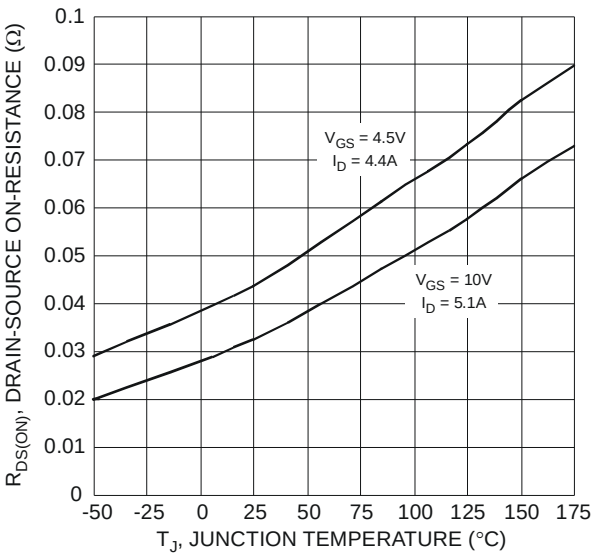


Figure 6 On-Resistance Variation with Temperature

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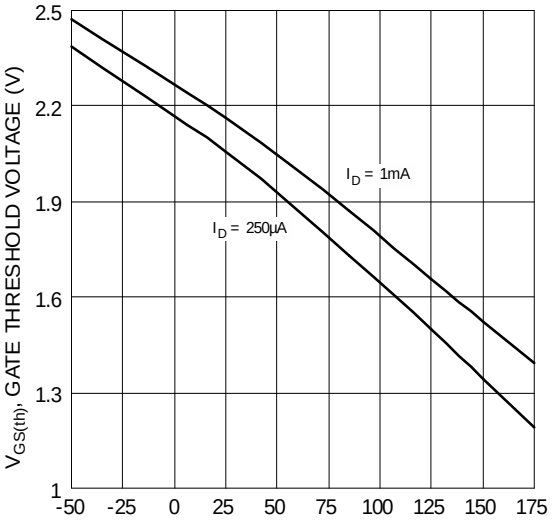


Figure 7 Gate Threshold Variation vs. Junction Temperature

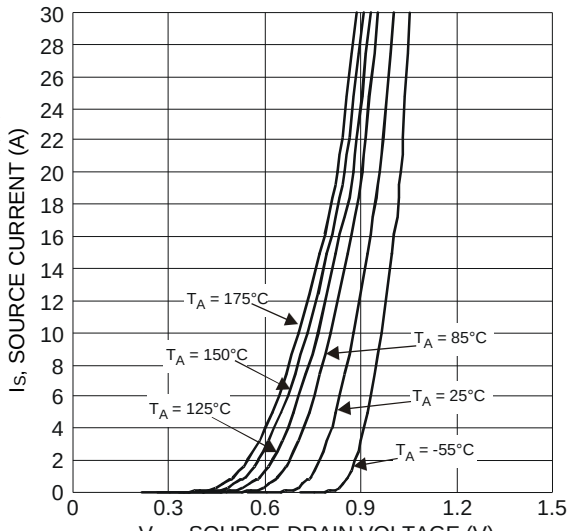


Figure 8 Diode Forward Voltage vs. Current

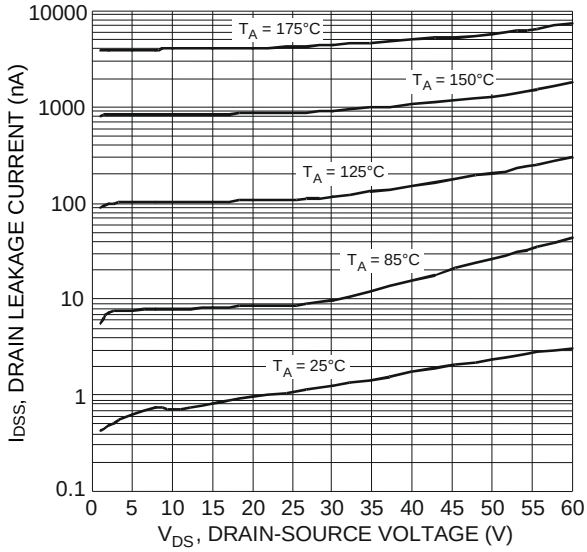


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

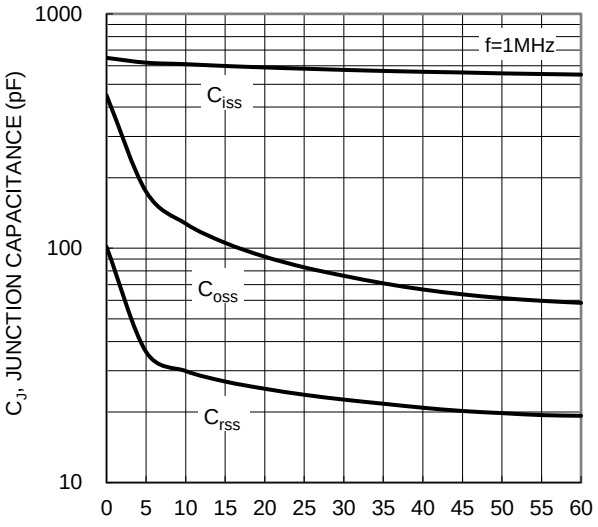


Figure 10 Typical Junction Capacitance

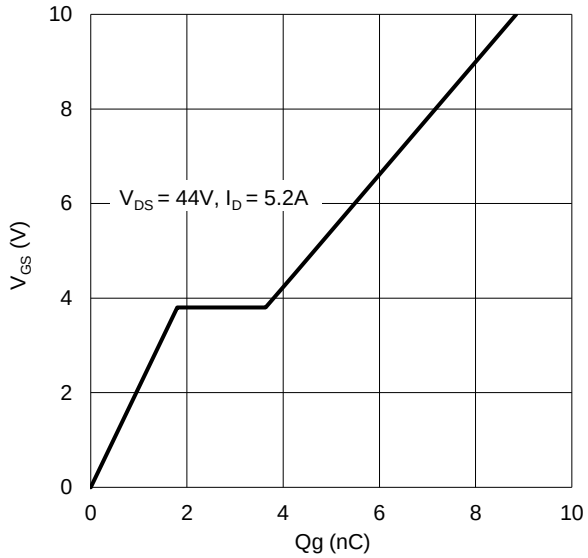


Figure 11 Gate Charge

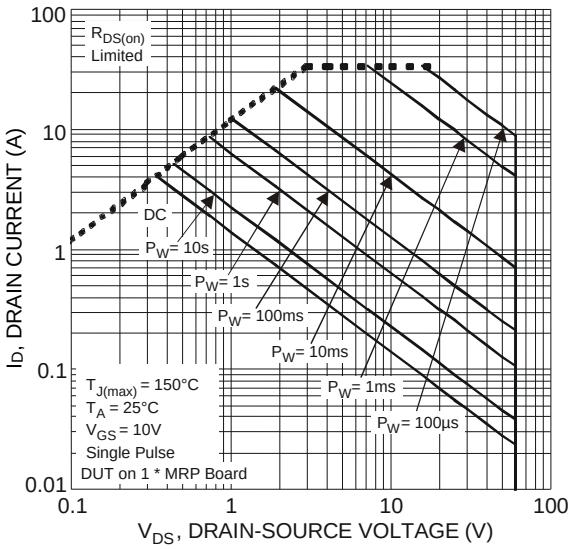


Figure 12 SOA, Safe Operation Area

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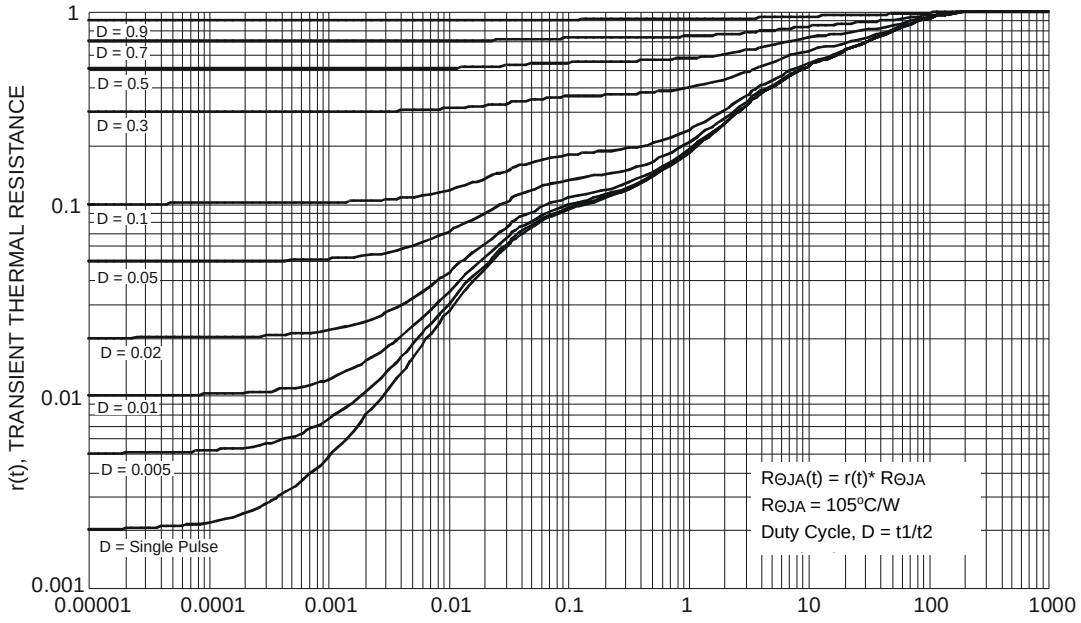


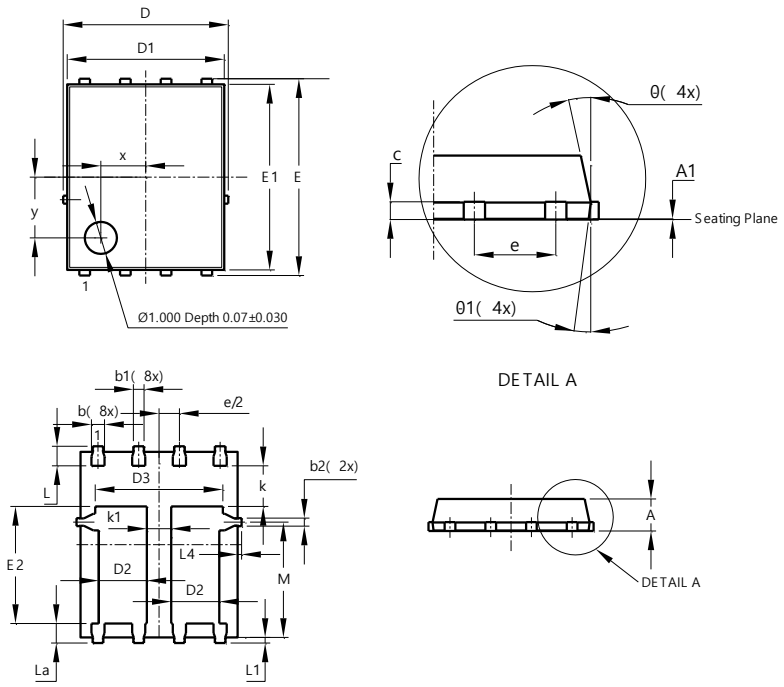
Figure 13 Transient Thermal Resistance

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)

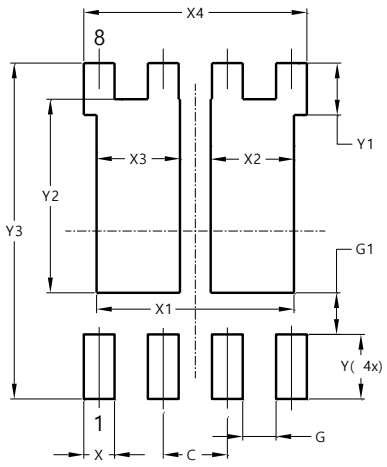


PowerDI5060-8 (Type C)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	1.40	1.60	1.50
D3	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.76	3.66
e	1.27BSC		
k	-	-	1.27
k1	0.56	-	-
L	0.51	0.71	0.61
La	0.51	0.71	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	1.650
X3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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